Nch 800V 8A Power MOSFET

V _{DSS}	800V
R _{DS(on)} (Max.)	1.03Ω
I _D	±8A
P_D	66W

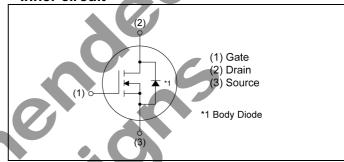
TO-220FM

Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Gate-source voltage (V_{GSS}) guaranteed to be $\pm 30V$.
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.
- 6) Pb-free lead plating; RoHS compliant

•Inner circuit

Outline



Packaging specifications

- i donaş	ing specifications	
	Packing	Bulk
	Reel size (mm)	-
	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	500
	Taping code	-
	Marking	R8008ANX

Application

Switching Power Supply

● Absolute maximum ratings (T_a = 25°C ,unless otherwise specified)

Parameter	Symbol	Value	Unit	
Drain - Source voltage		V_{DSS}	800	V
Continuous drain current	T _C = 25°C	I _D *1	±8	Α
Continuous drain current	T _C = 100°C	I _D *1	±3.9	Α
Pulsed drain current		l _{DP} *2	±32	Α
Gate - Source voltage		V_{GSS}	±30	V
Avalanche current, single pulse		I _{AS} *3	4	Α
Avalanche energy, single pulse		E _{AS} *3	4.2	mJ
Avalanche energy, repetitive		E _{AR} *4	3.3	mJ
Power dissipation (T _c = 25°C)		P _D	66	W
Junction temperature		T _j	150	°C
Operating junction and storage temper	T _{stg}	-55 to +150	°C	
Reverse diode dv/dt		dv/dt	15	V/ns

Absolute maximum ratings

Parameter	Symbol	Conditions	Values	Unit
Drain - Source voltage slope	dv/dt	$V_{DS} = 640V, I_{D} = 8A$ $T_{j} = 125^{\circ}C$	50	V/ns

●Thermal resistance

Parameter	Symbol	Values			Unit	
Parameter	Symbol	Min.	Тур.	Max.	Offic	
Thermal resistance, junction - case	R _{thJC}	-(-	1.87	°C/W	
Thermal resistance, junction - ambient	R _{thJA}		-	70	°C/W	
Soldering temperature, wavesoldering for 10s	T _{sold}		ı	265	°C	
●Electrical characteristics (T _a = 25°C)						
			Values			

● Electrical characteristics (T_a = 25°C)

Parameter	Symbol Conditions		Values			Unit
r al al nie lei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	V _{(BR)DS\$}	$V_{GS} = 0V$, $I_D = 1mA$	800	-	ı	V
Drain - Source avalanche breakdown voltage	V _{(BR)DS}	$V_{GS} = 0V$, $I_D = 4A$	ı	900	ı	V
		$V_{DS} = 800V, V_{GS} = 0V$				
Zero gate voltage drain current	I _{DSS}	$T_j = 25^{\circ}C$	-	0.1	100	μΑ
X.		$T_j = 125^{\circ}C$	-	-	1000	
Gate - Source leakage current	I _{GSS}	$V_{GS} = \pm 30V$, $V_{DS} = 0V$	1	-	±100	nA
Gate threshold voltage	$V_{GS(th)}$	V _{DS} = 10V, I _D = 1mA	3	-	5	V
		V _{GS} = 10V, I _D = 4.0A				
Static drain - source on - state resistance	R _{DS(on)} *6	$T_j = 25^{\circ}C$	-	0.79	1.03	Ω
on state regionality		$T_j = 125^{\circ}C$	-	1.54	-	
Gate resistance	R_G	f = 1MHz, open drain	-	6.6	-	Ω

● Electrical characteristics (T_a = 25°C)

Parameter	Cumbal	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Forward Transfer Admittance	Y _{fs} *6	V _{DS} = 10V, I _D = 4A	2.0	4.0	_	S
Input capacitance	C _{iss}	V _{GS} = 0V	-	1080		
Output capacitance	C _{oss}	V _{DS} = 25V	-	480)	pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	32	_	
Effective output capacitance, energy related	C _{o(er)}	V _{GS} = 0V,		30.2	-	. L
Effective output capacitance, time related	C _{o(tr)}	V _{DS} = 0V to 640V		78.8	-	pF
Turn - on delay time	t _{d(on)} *6	V _{DD} ≈ 400V, V _{GS} = 10V	-	32	-	
Rise time	t _r *6	I _D = 4.0A	(50	-	100
Turn - off delay time	t _{d(off)} *6	R _L ≃ 100Ω		85	170	ns
Fall time	t _f *6	$R_G = 10\Omega$	-	30	60	

● Gate charge characteristics (T_a = 25°C)

Parameter	Symbol	Symbol Conditions		Values		
r ai ai i le tei	Symbol	Conditions	Min.	Тур.	Max.	Unit
Total gate charge	Q _g *6	V _{DD} ≃ 400V	-	39	-	
Gate - Source charge	Q _{gs} *6	I _D = 8A	-	8.7	-	nC
Gate - Drain charge	Q _{gd} *6	V _{GS} = 10V	-	23	-	
Gate plateau voltage	V _(plateau)	$V_{DD} \simeq 400V$, $I_D = 8A$	-	7.3	-	V

^{*1} Limited only by maximum temperature allowed.

^{*2} Pw ≤ 10µs, Duty cycle ≤ 1%

^{*3} L $^{\sim}500\mu\text{H},\,\text{V}_{DD}$ =50V, R $_{G}$ =25 Ω , starting T $_{j}$ =25 $^{\circ}\text{C}$

^{*4} L $^\sim$ 500 μ H, V_{DD}=50V, R_G=25 Ω , starting T_j=25 $^\circ$ C, f=10kHz

^{*5} Reference measurement circuits Fig.5-1.

^{*6} Pulsed

●Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

	•	/ \ u	,			
Parameter	Symbol	Conditions	Values			Unit
raiainetei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Continuous forward current	I _S *1	T - 25°C	-	-	8	Α
Pulse forward current	I _{SP} *2	T _C = 25°C	-	-	32	А
Forward voltage	V _{SD} *6	$V_{GS} = 0V, I_{S} = 8A$	-	-	1.5	V
Reverse recovery time	t _{rr} *6		-	625	-	ns
Reverse recovery charge	Q _{rr} *6	I _S = 8A di/dt = 100A/µs		7.03	-	μC
Peak reverse recovery current	I _{rrm} *6	αναι 100/ γμο		22.5	-	Α
Peak rate of fall of reverse recovery current	di _{rr} /dt	T _j = 25°C).	90	-	A/µs

• Typical transient thermal characteristics

Symbol	Value	Unit
R _{th1}	0.144	
R _{th2}	0.72	K/W
R _{th3}	2.15	

Symbol	Value	Unit
C _{th1}	0.00267	
C _{th2}	0.0348	Ws/K
C _{th3}	0.491	

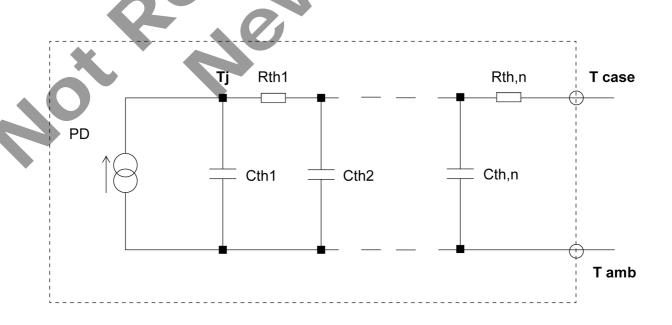


Fig.1 Power Dissipation Derating Curve

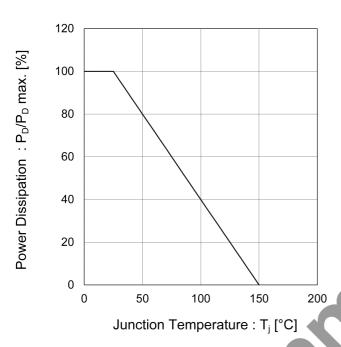


Fig.2 Maximum Safe Operating Area

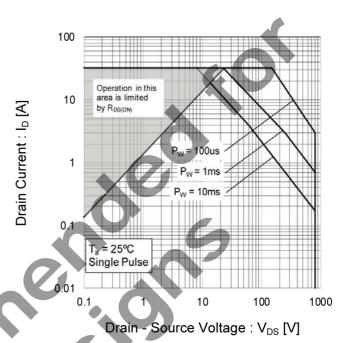
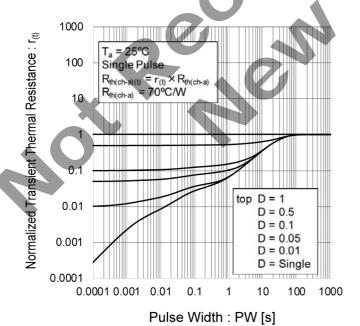


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width



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Avalanche Current : IAR [A]

Electrical characteristic curves

Fig.4 Avalanche Current vs. Inductive Load

Fig.5 Avalanche Power Losses

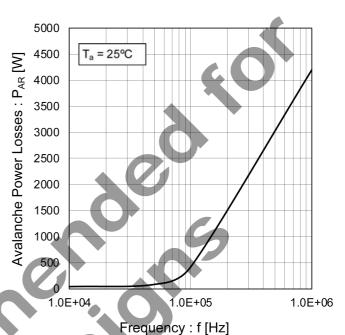
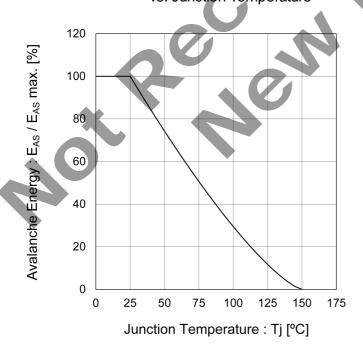
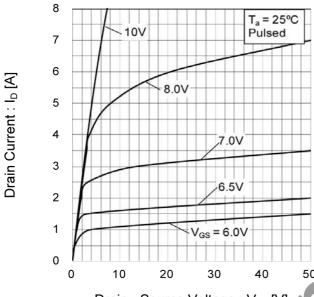


Fig.6 Avalanche Energy Derating Curve vs. Junction Temperature



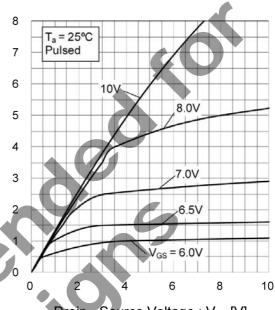
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Fig.7 Typical Output Characteristics(I)



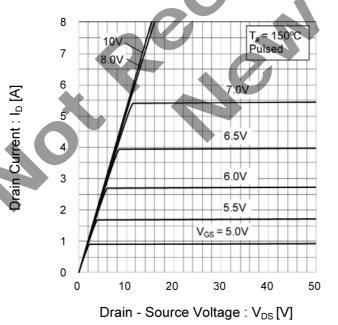
Drain - Source Voltage : $V_{DS}[V]$

Fig.8 Typical Output Characteristics(II)



Drain - Source Voltage : V_{DS} [V]

Fig.9 Tj = 150°C Typical Output Characteristics (l)



Drain Current : I_D [A]

Drain Current : I_D [A]

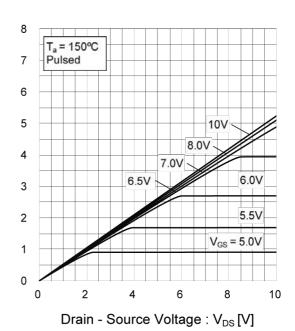


Fig.10 Tj = 150°C Typical Output Characteristics (II)

Fig.11 Breakdown Voltage vs. Junction Temperature

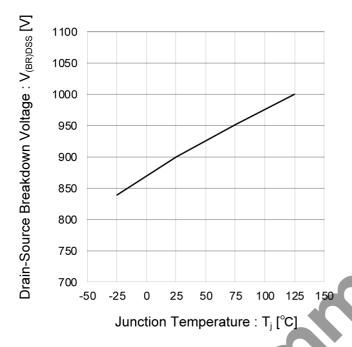


Fig.12 Typical Transfer Characteristics

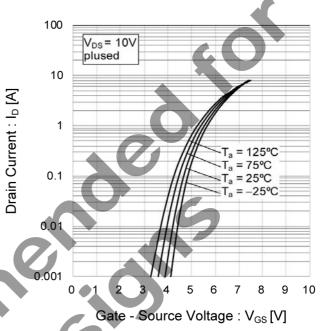


Fig.13 Gate Threshold Voltage vs Junction Temperature

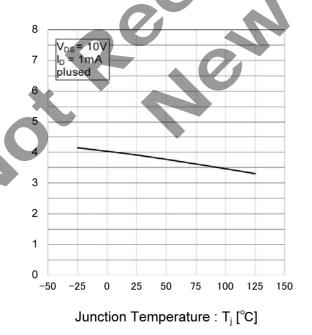
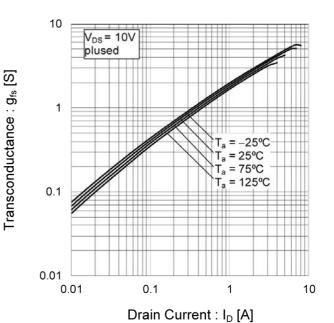


Fig.14 Transconductance vs. Drain Current



Gate Threshold Voltage: V_{GS(th)} [V]

8/13

Static Drain - Source On-State Resistance : $R_{\text{DS}(\text{on})}\left[\Omega\right]$

• Electrical characteristic curves

Fig.15 Static Drain - Source On - State Resistance vs. Gate Source Voltage

T_a=25°C pulsed

2

I_b=4.0A

1

0

0

5

10

15

26

Gate - Source Voltage : V_{GS} [V]

Fig.16 Static Drain - Source On - State Resistance vs. Junction Temperature

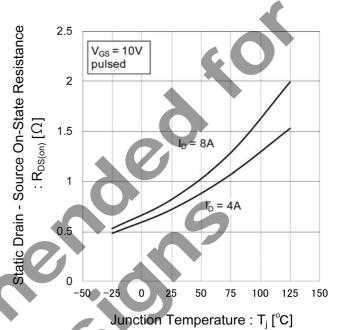


Fig.17 Static Drain - Source On - State Resistance vs. Drain Current

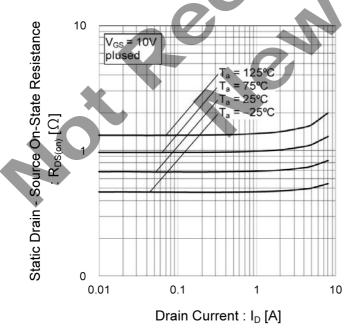
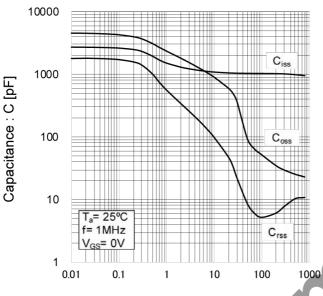
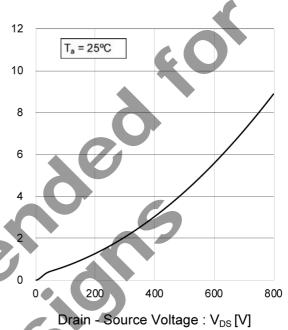


Fig.18 Typical Capacitance vs. Drain - Source Voltage



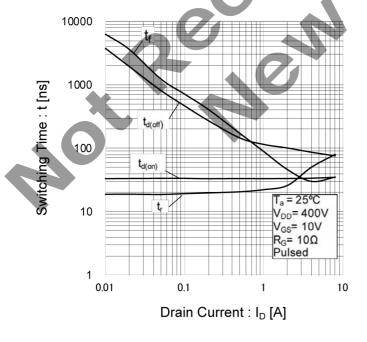
Drain - Source Voltage : V_{DS} [V]

Fig.19 Coss Stored Energy



The country contage

Fig.20 Switching Characteristics



Gate - Source Voltage : V_{GS} [V]

Coss Stored Energy : $\mathsf{E}_{ extsf{oss}}\left[\mu
ight]$

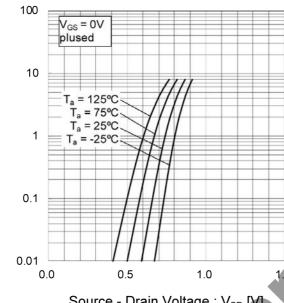
15
10
5
T_a= 25°C
V_{DD}= 400V
I_D= 8A
Pulsed
0 10 20 30 40 50 60
Total Gate Charge : Q_q [nC]

Fig.21 Dynamic Input Characteristics

Inverse Diode Forward Current : Is [A]

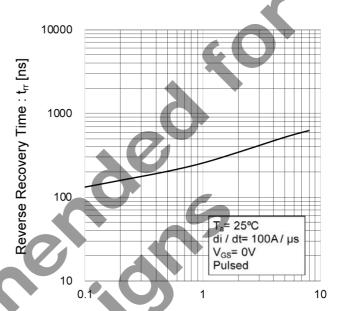
Electrical characteristic curves

Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage



Source - Drain Voltage : V_{SD} [V]

Fig.23 Reverse Recovery Time vs. Inverse Diode Forward Current



Inverse Diode Forward Current: Is [A]

Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

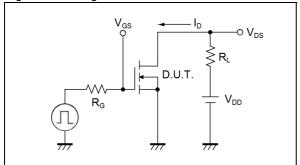


Fig.2-1 Gate Charge Measurement Circuit

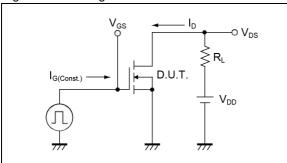


Fig.3-1 Avalanche Measurement Circuit

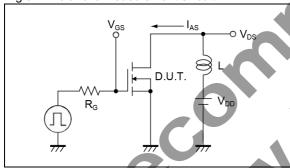


Fig.4-1 dv/dt Measurement Circuit

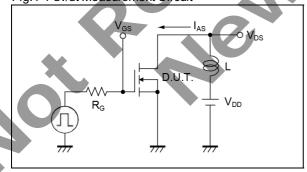


Fig.5-1 di/dt Measurement Circuit

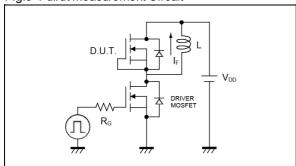


Fig.1-2 Switching Waveforms

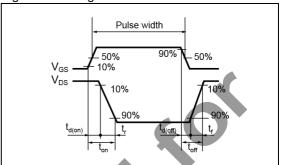


Fig.2-2 Gate Charge Waveform

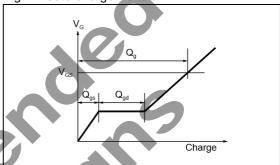


Fig.3-2 Avalanche Waveform

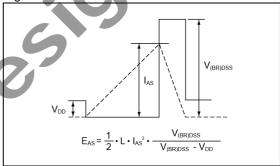


Fig.4-2 dv/dt Waveform

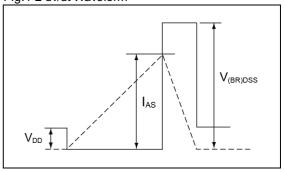
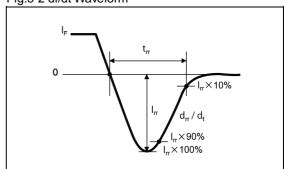
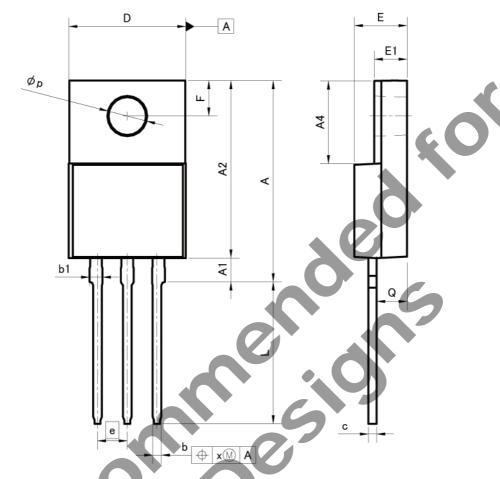


Fig.5-2 di/dt Waveform



Dimensions

TO-220FM



D.114	MILIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
A	16.60	17.60	0.654	0.693
A1	1.80	2.20	0.071	0.087
A2	14.80	15.40	0.583	0.606
A4	6.80	7.20	0.268	0.283
b	0.70	0.90	0.028	0.035
b1	1.10	1.50	0.043	0.059
С	0.70	0.85	0.028	0.033
D	9.90	10.30	0.390	0.406
E	4.40	4.80	0.173	0.189
е	2.	54	0.1	00
E1	2.70	3.00	0.106	0.118
F	2.80	3.20	0.110	0.126
L	11.50	12.50	0.453	0.492
р	3.00	3.40	0.118	0.134
Q	2.10	3.10	0.083	0.122
Х	9 — 8	0.38	226	0.015

Dimension in mm/inches



Notice

Precaution on using ROHM Products

1. Our Products are designed and manufactured for application in ordinary electronic equipments (such as AV equipment, OA equipment, telecommunication equipment, home electronic appliances, amusement equipment, etc.). If you intend to use our Products in devices requiring extremely high reliability (such as medical equipment (Note 1), transport equipment, traffic equipment, aircraft/spacecraft, nuclear power controllers, fuel controllers, car equipment including car accessories, safety devices, etc.) and whose malfunction or failure may cause loss of human life, bodily injury or serious damage to property ("Specific Applications"), please consult with the ROHM sales representative in advance. Unless otherwise agreed in writing by ROHM in advance, ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of any ROHM's Products for Specific Applications.

(Note1) Medical Equipment Classification of the Specific Applications

JAPAN	USA	EU	CHINA
CLASSⅢ	CLASSIII	CLASS II b	CLASSIII
CLASSIV		CLASSⅢ	

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 - [b] Installation of redundant circuits to reduce the impact of single or multiple circuit failure
- 3. Our Products are designed and manufactured for use under standard conditions and not under any special or extraordinary environments or conditions, as exemplified below. Accordingly, ROHM shall not be in any way responsible or liable for any damages, expenses or losses arising from the use of any ROHM's Products under any special or extraordinary environments or conditions. If you intend to use our Products under any special or extraordinary environments or conditions (as exemplified below), your independent verification and confirmation of product performance, reliability, etc, prior to use, must be necessary:
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 - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
 - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl₂, H₂S, NH₃, SO₂, and NO₂
 - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
 - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
 - [f] Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
 - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse, is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power, exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

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- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
- 2. You agree that application notes, reference designs, and associated data and information contained in this document are presented only as guidance for Products use. Therefore, in case you use such information, you are solely responsible for it and you must exercise your own independent verification and judgment in the use of such information contained in this document. ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of such information.

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This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

Precaution for Storage / Transportation

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
 - [a] the Products are exposed to sea winds or corrosive gases, including Cl2, H2S, NH3, SO2, and NO2
 - [b] the temperature or humidity exceeds those recommended by ROHM
 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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